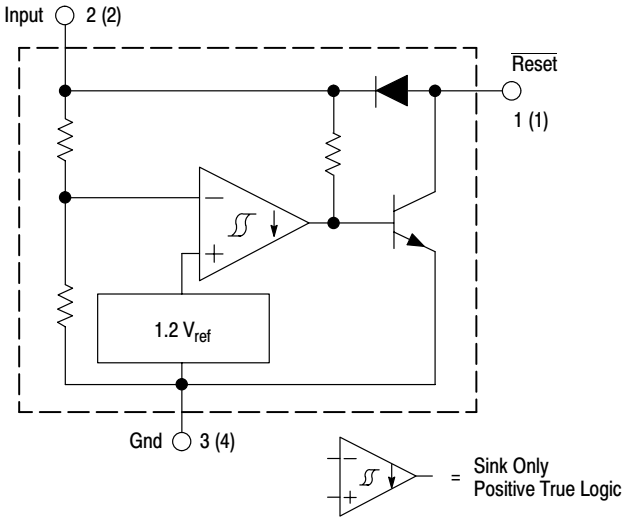
MC34164, MC33164

Micropower Undervoltage Sensing Circuits

The MC34164 series are undervoltage sensing circuits specifically designed for use as reset controllers in portable microprocessor based systems where extended battery life is required. These devices offer the designer an economical solution for low voltage detection with a single external resistor. The MC34164 series features a bandgap reference, a comparator with precise thresholds and built–in hysteresis to prevent erratic reset operation, an open collector reset output capable of sinking in excess of 6.0 mA, and guaranteed operation down to 1.0 V input with extremely low standby current. These devices are packaged in 3–pin TO–226AA, 8–pin SO–8 and Micro8™ surface mount packages.

Applications include direct monitoring of the 3.0 or 5.0 V MPU/logic power supply used in appliance, automotive, consumer, and industrial equipment.

- Temperature Compensated Reference
- Monitors 3.0 V (MC34164–3) or 5.0 V (MC34164–5) Power Supplies
- Precise Comparator Thresholds Guaranteed Over Temperature
- Comparator Hysteresis Prevents Erratic Reset
- Reset Output Capable of Sinking in Excess of 6.0 mA
- Internal Clamp Diode for Discharging Delay Capacitor
- Guaranteed Reset Operation With 1.0 V Input
- Extremely Low Standby Current: As Low as 9.0 μA
- Economical TO–226AA, SO–8 and Micro8 Surface Mount Packages



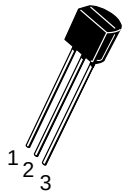
Pin numbers adjacent to terminals are for the 3–pin TO–226AA package.
Pin numbers in parenthesis are for the 8–lead packages.

This device contains 28 active transistors.

Figure 1. Representative Block Diagram

ON Semiconductor

http://onsemi.com

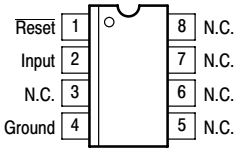


TO–226AA
P SUFFIX
CASE 29

SO–8
D SUFFIX
CASE 751

Micro8
DM SUFFIX
CASE 846A

PIN CONNECTIONS



(Top View)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 7 of this data sheet.

DEVICE MARKING INFORMATION

See general marking information in the device marking section on page 7 of this data sheet.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Power Input Supply Voltage	V_{in}	–1.0 to 12	V
$\overline{\text{Reset}}$ Output Voltage	V_O	–1.0 to 12	V
$\overline{\text{Reset}}$ Output Sink Current	I_{Sink}	Internally Limited	mA
Clamp Diode Forward Current, Pin 1 to 2 (Note 1)	I_F	100	mA
Power Dissipation and Thermal Characteristics P Suffix, Plastic Package Maximum Power Dissipation @ T_A = 25°C Thermal Resistance, Junction–to–Air D Suffix, Plastic Package Maximum Power Dissipation @ T_A = 25°C Thermal Resistance, Junction–to–Air DM Suffix, Plastic Package Maximum Power Dissipation @ T_A = 25°C Thermal Resistance, Junction–to–Air	 P_D $R_{\theta JA}$ P_D $R_{\theta JA}$ P_D $R_{\theta JA}$	 700 178 700 178 520 240	 mW °C/W mW °C/W mW °C/W
Operating Junction Temperature	T_J	+150	°C
Operating Ambient Temperature Range MC34164 Series MC33164 Series	T_A	 0 to +70 – 40 to +125	°C
Storage Temperature Range	T_{stg}	– 65 to +150	°C

NOTE: ESD data available upon request.

MC34164–3, MC33164–3 SERIES

ELECTRICAL CHARACTERISTICS (For typical values T_A = 25°C, for min/max values T_A is the operating ambient temperature range that applies [Notes 2 & 3], unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
COMPARATOR					
Threshold Voltage High State Output (V_{in} Increasing) Low State Output (V_{in} Decreasing) Hysteresis (I_{Sink} = 100 μA)	 V_{IH} V_{IL} V_H	 2.55 2.55 0.03	 2.71 2.65 0.06	 2.80 2.80 –	V
$\overline{\text{RESET}}$ OUTPUT					
Output Sink Saturation (V_{in} = 2.4 V, I_{Sink} = 1.0 mA) (V_{in} = 1.0 V, I_{Sink} = 0.25 mA)	V_{OL}	 – –	 0.14 0.1	 0.4 0.3	V
Output Sink Current (V_{in}, $\overline{\text{Reset}}$ = 2.4 V)	I_{Sink}	6.0	12	30	mA
Output Off–State Leakage (V_{in}, $\overline{\text{Reset}}$ = 3.0 V) (V_{in}, $\overline{\text{Reset}}$ = 10 V)	$I_{\overline{R}}$(leak)	 – –	 0.02 0.02	 0.5 1.0	μA
Clamp Diode Forward Voltage, Pin 1 to 2 (I_F = 5.0 mA)	V_F	6.0	0.9	1.2	V
TOTAL DEVICE					
Operating Input Voltage Range	V_{in}	1.0 to 10	–	–	V
Quiescent Input Current V_{in} = 3.0 V V_{in} = 6.0 V	I_{in}	 – –	 9.0 24	 15 40	μA

1. Maximum package power dissipation limits must be observed.
2. Low duty cycle pulse techniques are used during test to maintain junction temperature as close to ambient as possible.
3. T_{low} = 0°C for MC34164 T_{high} = +70°C for MC34164
   = – 40°C for MC33164 = +125°C for MC33164

MC34164–5, MC33164–5 SERIES

ELECTRICAL CHARACTERISTICS (For typical values T_A = 25°C, for min/max values T_A is the operating ambient temperature range that applies [Notes 5 & NO TAG], unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
COMPARATOR					
Threshold Voltage					V
High State Output (V_{in} Increasing)	V_{IH}	4.15	4.33	4.45	
Low State Output (V_{in} Decreasing)	V_{IL}	4.15	4.27	4.45	
Hysteresis (I_{Sink} = 100 μA)	V_H	0.02	0.09	–	
$\overline{\text{RESET}}$ OUTPUT					
Output Sink Saturation	V_{OL}				V
(V_{in} = 4.0 V, I_{Sink} = 1.0 mA)		–	0.14	0.4	
(V_{in} = 1.0 V, I_{Sink} = 0.25 mA)		–	0.1	0.3	
Output Sink Current (V_{in}, $\overline{\text{Reset}}$ = 4.0 V)	I_{Sink}	7.0	20	50	mA
Output Off–State Leakage	$I_{\overline{R}}$(leak)				μA
(V_{in}, $\overline{\text{Reset}}$ = 5.0 V)		–	0.02	0.5	
(V_{in}, $\overline{\text{Reset}}$ = 10 V)		–	0.02	2.0	
Clamp Diode Forward Voltage, Pin 1 to 2 (I_F = 5.0 mA)	V_F	0.6	0.9	1.2	V
TOTAL DEVICE					
Operating Input Voltage Range	V_{in}	1.0 to 10	–	–	V
Quiescent Input Current	I_{in}				μA
V_{in} = 5.0 V		–	12	20	
V_{in} = 10 V		–	32	50	

4. Maximum package power dissipation limits must be observed.
5. Low duty cycle pulse techniques are used during test to maintain junction temperature as close to ambient as possible.
6. T_{low} = 0°C for MC34164 T_{high} = +70°C for MC34164
   = – 40°C for MC33164 = +125°C for MC33164

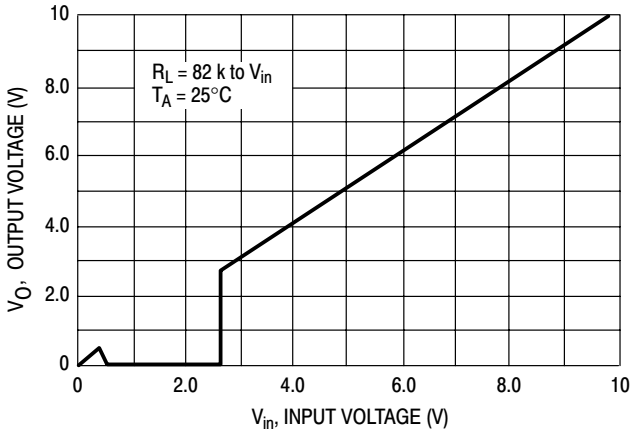


Figure 1. MC3X164–3 $\overline{\text{Reset}}$ Output Voltage versus Input Voltage

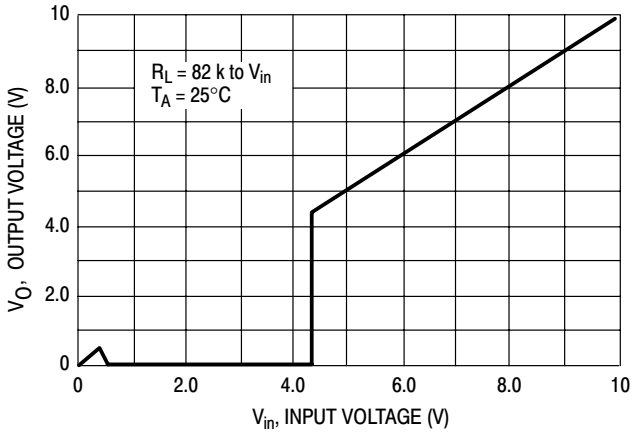


Figure 2. MC3X164–5 $\overline{\text{Reset}}$ Output Voltage versus Input Voltage

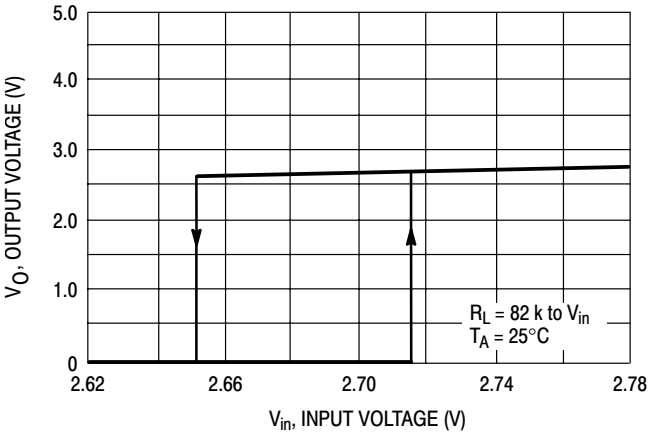


Figure 3. MC3X164–3 $\overline{\text{Reset}}$ Output Voltage versus Input Voltage

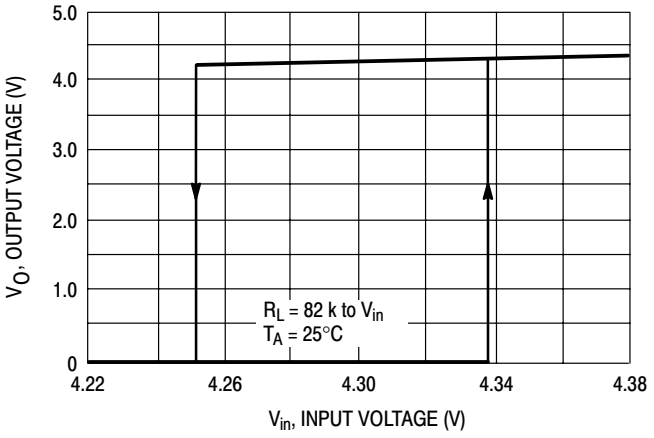


Figure 4. MC3X164–5 $\overline{\text{Reset}}$ Output Voltage versus Input Voltage

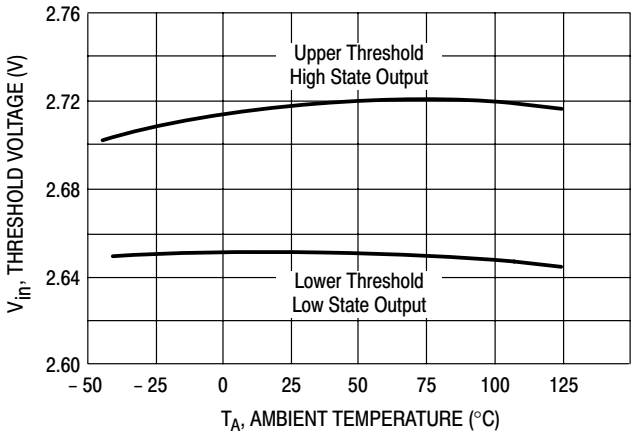


Figure 5. MC3X164–3 Comparator Threshold Voltage versus Temperature

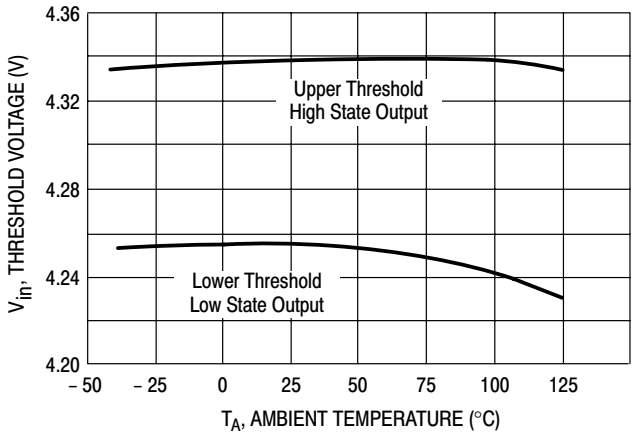


Figure 6. MC3X164–5 Comparator Threshold Voltage versus Temperature

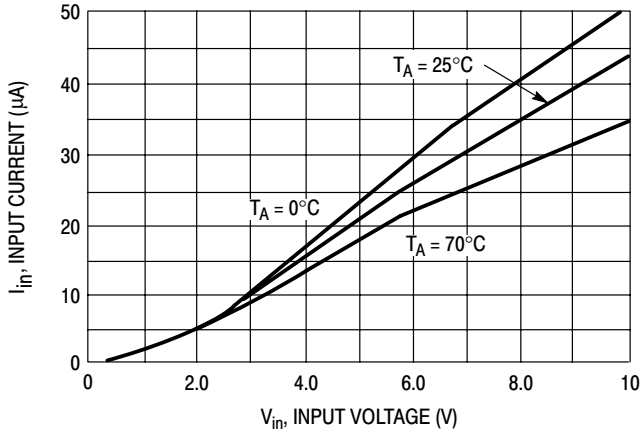


Figure 7. MC3X164–3 Input Current versus Input Voltage

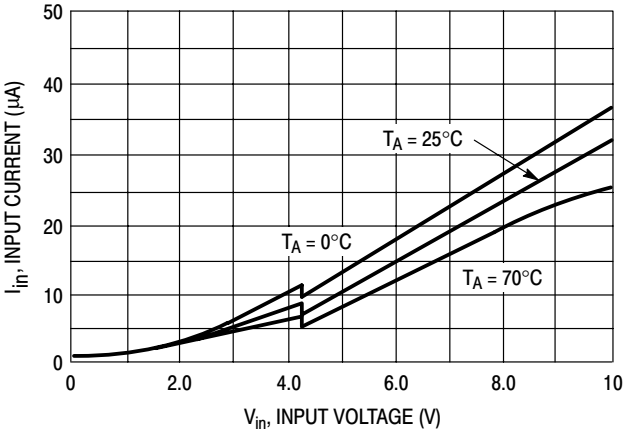


Figure 8. MC3X164–5 Input Current versus Input Voltage

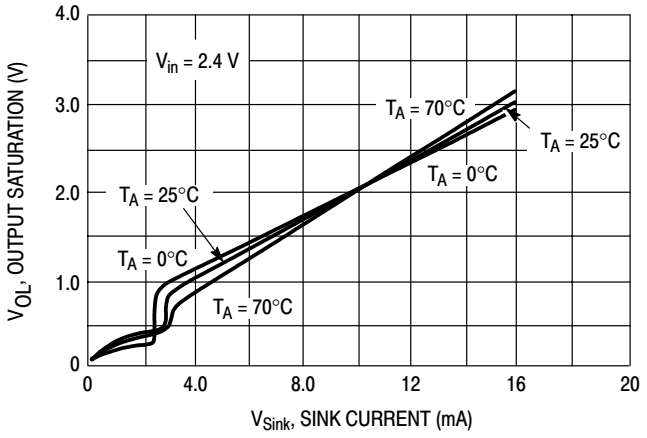


Figure 9. MC3X164–3 $\overline{\text{Reset}}$ Output Saturation versus Sink Current

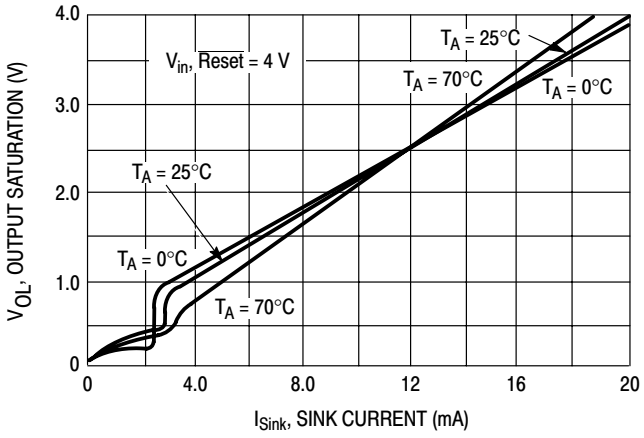


Figure 10. MC3X164–5 $\overline{\text{Reset}}$ Output Saturation versus Sink Current

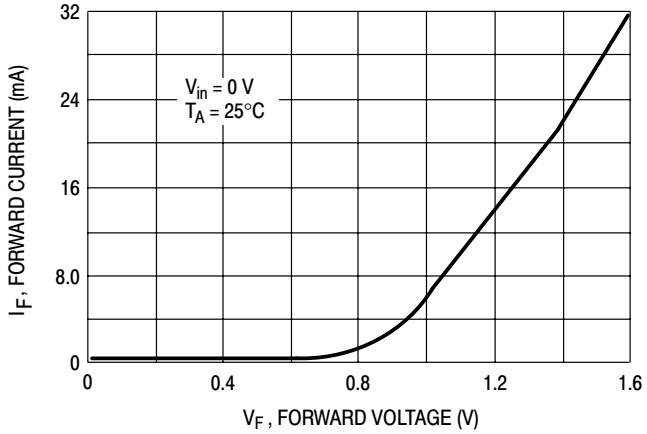


Figure 11. Clamp Diode Forward Current versus Voltage

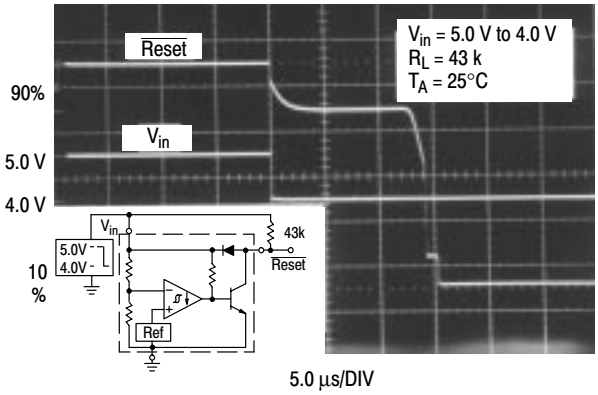
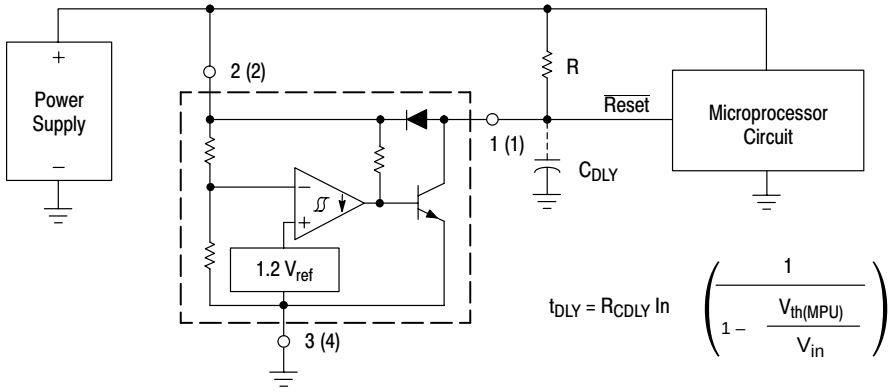
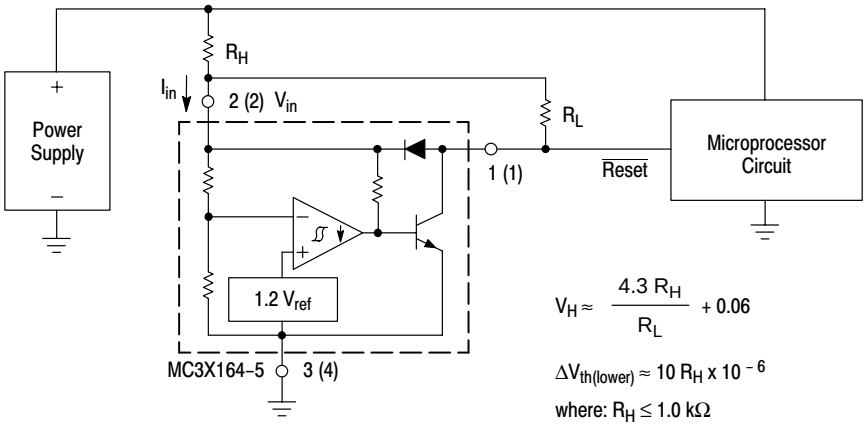


Figure 12. $\overline{\text{Reset}}$ Delay Time (MC3X164–5 Shown)



A time delayed reset can be accomplished with the addition of C_{DLY}. For systems with extremely fast power supply rise times (< 500 ns) it is recommended that the RCDLY time constant be greater than 5.0 μs. $V_{th(MPU)}$ is the microprocessor reset input threshold.

Figure 13. Low Voltage Microprocessor Reset



Test Data			
V_H (mV)	ΔV_{th} (mV)	R_H (Ω)	R_L (kΩ)
60	0	0	43
103	1.0	100	10
123	1.0	100	6.8
160	1.0	100	4.3
155	2.2	220	10
199	2.2	220	6.8
280	2.2	220	4.3
262	4.7	470	10
306	4.7	470	8.2
357	4.7	470	6.8
421	4.7	470	5.6
530	4.7	470	4.3

Comparator hysteresis can be increased with the addition of resistor R_H. The hysteresis equation has been simplified and does not account for the change of input current I_{in} as V_{in} crosses the comparator threshold (Figure 8). An increase of the lower threshold $\Delta V_{th(lower)}$ will be observed due to I_{in} which is typically 10 μA at 4.3 V. The equations are accurate to ±10% with R_H less than 1.0 kΩ and R_L between 4.3 kΩ and 43 kΩ.

Figure 14. Low Voltage Microprocessor Reset With Additional Hysteresis (MC3X164–5 Shown)

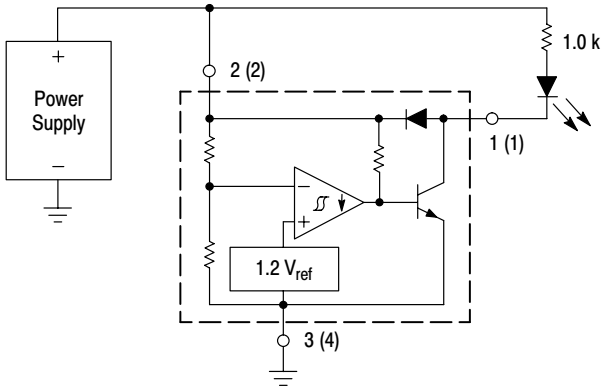


Figure 15. Voltage Monitor

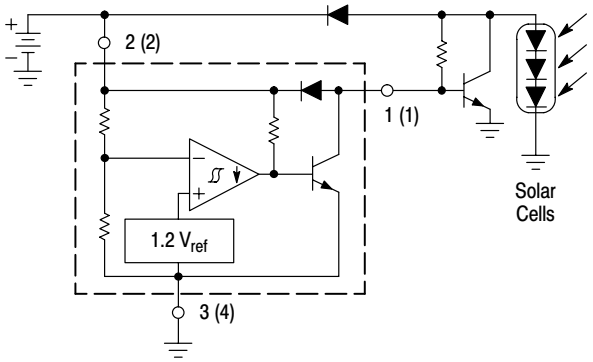
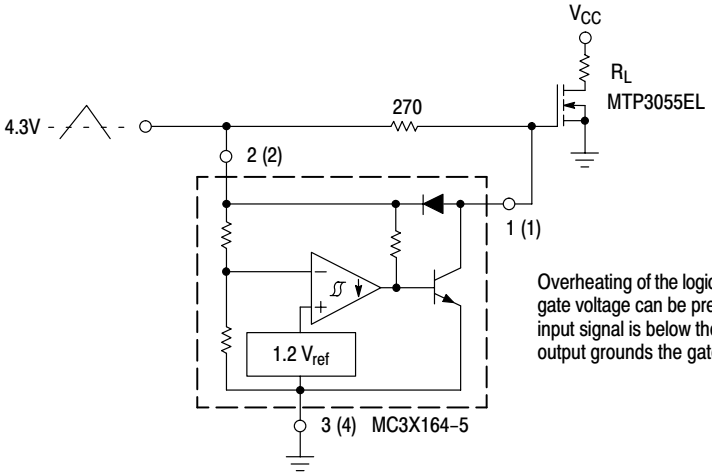


Figure 16. Solar Powered Battery Charger



Overheating of the logic level power MOSFET due to insufficient gate voltage can be prevented with the above circuit. When the input signal is below the 4.3 V threshold of the MC3X164–5, its output grounds the gate of the L^2 MOSFET.

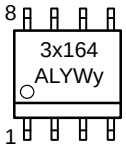
Figure 17. MOSFET Low Voltage Gate Drive Protection Using the MC3X164–5

ORDERING INFORMATION

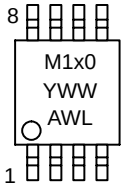
Device	Package	Shipping
MC33164D–3	SO–8	98 Units / Rail
MC33164D–3R2	SO–8	2500 Units / Tape & Reel
MC33164DM–3R2	Micro8	4000 Units / Tape & Reel
MC33164P–3	TO–92	2000 Units / Box
MC33164P–3RA	TO–92	2000 Units / Tape & Reel
MC33164P–3RP	TO–92	2000 Units / Pack
MC33164D–5	SO–8	98 Units / Rail
MC33164D–5R2	SO–8	2500 Units / Tape & Reel
MC33164DM–5R2	Micro8	4000 Units / Tape & Reel
MC33164P–5	TO–92	2000 Units / Box
MC33164P–5RA	TO–92	2000 Units / Tape & Reel
MC33164P–5RP	TO–92	2000 Units / Pack
MC34164D–3	SO–8	98 Units / Rail
MC34164D–3R2	SO–8	2500 Units / Tape & Reel
MC34164DM–3R2	Micro8	4000 Units / Tape & Reel
MC334164P–3	TO–92	2000 Units / Box
MC34164P–3RP	TO–92	2000 Units / Pack
MC34164D–5	SO–8	98 Units / Rail
MC34164D–5R2	SO–8	2500 Units / Tape & Reel
MC34164DM–5R2	Micro8	4000 Units / Tape & Reel
MC334164P–5	TO–92	2000 Units / Box
MC34164P–5RA	TO–92	2000 Units / Tape & Reel
MC34164P–5RP	TO–92	2000 Units / Pack

MARKING DIAGRAMS

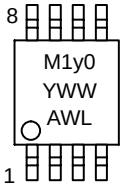
SO–8
D SUFFIX
CASE 751



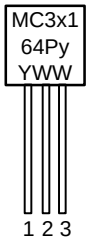
Micro8
MC33164DM
CASE 846A



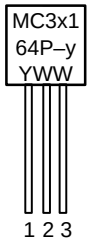
Micro8
MC34164DM
CASE 846A



TO–92
MC3x164P–y
CASE 29



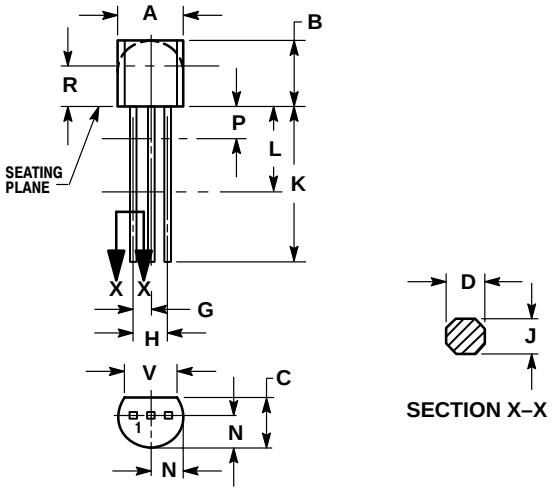
TO–92
MC3x164P–yRA
MC3x164P–yRP
CASE 29



x = Device Number 3 or 4
y = Suffix Number 3 or 5
A = Assembly Location
WL, L = Wafer Lot
YY, Y = Year
WW, W = Work Week

PACKAGE DIMENSIONS

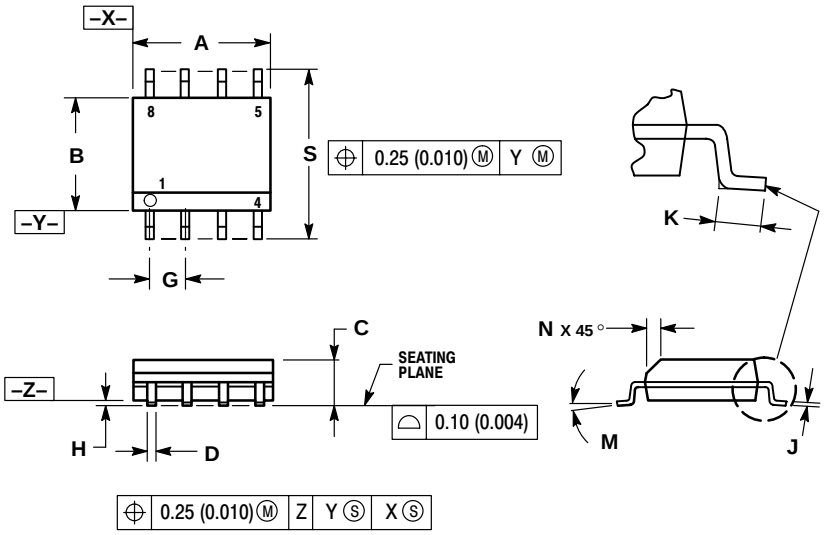
TO–226AA
P SUFFIX
CASE 29–11
ISSUE AL



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.115	---	2.93	---
V	0.135	---	3.43	---

SO–8
D SUFFIX
CASE 751–07
ISSUE W

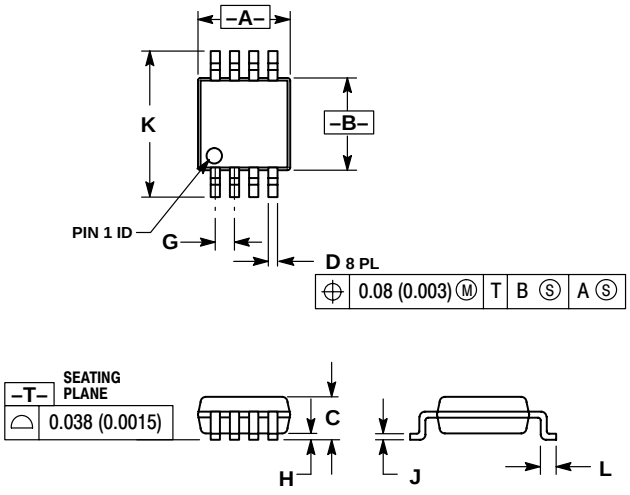


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	4.80	5.00	0.189	0.197
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27 BSC		0.050 BSC	
H	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
M	0 °	8 °	0 °	8 °
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

PACKAGE DIMENSIONS

Micro8
DM SUFFIX
CASE 846A–02
ISSUE E



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	2.90	3.10	0.114	0.122
B	2.90	3.10	0.114	0.122
C	---	1.10	---	0.043
D	0.25	0.40	0.010	0.016
G	0.65 BSC		0.026 BSC	
H	0.05	0.15	0.002	0.006
J	0.13	0.23	0.005	0.009
K	4.75	5.05	0.187	0.199
L	0.40	0.70	0.016	0.028

Notes

Notes

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